

# Xiao-Yu Zhang

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Simulation Study of Lateral Schottky Barrier IMPATT Diode Based on AlGaIn/GaN 2-DEG for Terahertz Applications. IEEE Transactions on Electron Devices, 2022, 69, 1006-1013.	3.0	5
2	Improved performance of Ni/GaN Schottky barrier impact ionization avalanche transit time diode with n-type GaN deep level defects. Semiconductor Science and Technology, 2021, 36, 025001.	2.0	5
3	Negative differential resistance characteristics of GaN-based resonant tunneling diodes with quaternary AlInGaIn as barrier. Semiconductor Science and Technology, 2021, 36, 015018.	2.0	1
4	Optimized Design of Ni/GaN Schottky Barrier IMPATT Diode With n-type GaN Deep Level Defects. , 2021, , .		1
5	Noise characteristics of Ni/GaN Schottky barrier IMPATT diode based on polar- and nonpolar-oriented wurtzite GaN for terahertz application. Superlattices and Microstructures, 2020, 139, 106405.	3.1	8